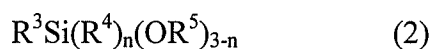
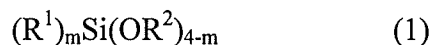


Amendments to the Claims:

1. (Previously Presented) A composition for forming porous film, comprising a surfactant and

a solution comprising polymer obtainable by hydrolyzing and condensing, in the presence of the surfactant, one or more alkoxysilanes represented by Formula (1) and one or more alkoxysilanes represented by Formula (2):



wherein R^1 represents a straight chain or branched alkyl group having 1 to 7 carbons or an aryl group wherein the alkyl or aryl group may be substituted or non-substituted and when there are R^1 's, the R^1 's are independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons and when there are R^2 's, the R^2 's are independently the same or different; R^3 represents a straight chain or branched alkyl group having 8 to 30 carbons; R^4 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^4 's, the R^4 's are independently the same or different; R^5 represents an alkyl group having 1 to 4 carbons and when there are R^5 's, the R^5 's are independently the same or different; m is an integer of 0 to 3; and n is an integer of 0 to 2,

wherein the one or more alkoxysilanes represented by Formula (1) comprise one or more tetraalkoxysilanes wherein $m=0$ and one or more alkoxysilanes wherein $m=1, 2$ or 3 , and

wherein said one or more alkoxysilanes represented by Formula (2) is present in an amount of 0.01 to 10 parts by weight to 100 parts by weight of said one or more alkoxysilanes represented by Formula (1).

2. (Original) The composition for forming porous film according to Claim 1 wherein said surfactant is a compound which decomposes, evaporates or sublimates when heated to 400°C or less.

3. (Canceled)

4. (Previously Presented) The composition for forming porous film according to Claim 1 wherein said one or more of the alkoxysilanes represented by Formula (1) is 10% by weight or more of tetraalkoxysilane.

5. (Previously Presented) The composition for forming porous film according to Claim 1, comprising a compound which is neutral at ordinary temperature and generates acid or alkali at 80 to 200°C.

6. (Previously Presented) A method for forming porous film comprising a step of applying said composition of Claim 1 on a substrate to form film and a step of transforming the film into porous film.

7. (Original) The method for forming porous film according to Claim 6 wherein said step of transforming comprises a step of drying said film and a step of removing said surfactant from the dried film.

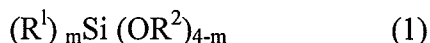
8. (Previously Presented) The method for forming porous film according to Claim 6 wherein said step of transforming comprises heating at 150 to 400°C.

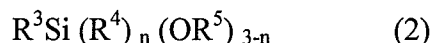
9. (Previously Presented) A porous film obtainable from said composition of Claim 1.

10. (Previously Presented) An interlevel insulator film formable by said composition of Claim 1.

11. (Currently Amended) A semiconductor device comprising an internal porous film which is formable by a composition for forming said porous film, comprising a surfactant and

a solution comprising polymer obtainable by hydrolyzing and condensing, in the presence of the surfactant, one or more of alkoxysilane represented by Formula (1) and one or more of alkoxysilane represented by Formula (2):





wherein R^1 represents a straight chain or branched alkyl group having 1 to 7 carbons or an aryl group wherein the alkyl or aryl group may be substituted or non-substituted and when there are R^1 s, the R^1 s are independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons and when there are R^2 s, the R^2 s are independently the same or different; R^3 represents a straight chain or branched alkyl group having 8 to 30 carbons; R^4 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^4 s, the R^4 s are independently the same or different; R^5 represents an alkyl group having 1 to 4 carbons and when there are R^5 s, the R^5 s are independently the same or different; m is an integer of 0 to 3; and n is an integer of 0 to 2,

wherein the one or more alkoxysilanes represented by Formula (1) comprise one or more tetraalkoxysilanes wherein m=0 and one or more alkoxysilanes wherein m=1, 2 or 3, and

wherein said one or more alkoxysilanes represented by Formula (2) is present in an amount of 0.01 to 10 parts by weight to 100 parts by weight of said one or more alkoxysilanes represented by Formula (1).

12. (Original) The semiconductor device according to Claim 11 wherein said surfactant is a compound which decomposes, evaporates or sublimates when heated to 400°C or less.

13. (Canceled)

14. (Previously Presented) The semiconductor device according to Claim 11 wherein said one or more of the alkoxysilanes represented by Formula (1) is 10% by weight or more of tetraalkoxysilane.

15. (Previously Presented) The semiconductor device according to Claim 11, comprising a compound which is neutral at ordinary temperature and generates acid or alkali at 80 to 200°C.

Application No.: 10/706,861
Amendment Dated July 19, 2007
Reply to Office Action of April 19, 2007

16. (Previously Presented) The semiconductor device according to Claim 11 wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.